

10/798,700

Please replace the paragraph that begins on page 4, line 20 with the following amended paragraph:

It is the object of embodiments of the present invention to provide a field effect transistor ~~with a capacity~~ having a capacitance that is substantially independent of the drain voltage between a drain area and a substrate.

SMC 12/14/00 Please replace the paragraph that begins on page ¹⁰4, line ¹26 with the following amended paragraph:

A substantial advantage of the present invention is that from a predetermined minimum drain voltage on, at which the space charge zones, as mentioned, completely fill both the columns or lamellae of the area and the substrate material in their surroundings, a spatial expansion and in particular the thickness of this depletion zone is substantially only dependent on the geometry of these columns or lamellae and no longer on the drain voltage. The ~~capacity~~ capacitance between the drain area and the substrate is then largely independent of the drain voltage. This enables simple, inexpensive, and efficient high-frequency matching of a circuit in which the inventive field effect transistor is used to the field effect transistor.